

ETCHING METHOD AND PLASMA PROCESSING SYSTEM

ABSTRACT

An etching method is implementable with a plasma processing apparatus including a chamber. The method includes (a) providing, in the chamber, a substrate including an etching
5 target film and a mask on the etching target film, and (b) etching the etching target film using plasma generated from a process gas including a hydrogen fluoride gas. The mask contains at least one metal selected from the group consisting of tungsten, molybdenum, ruthenium, titanium, indium, gallium, and zinc.

Fig. 1